

Features :

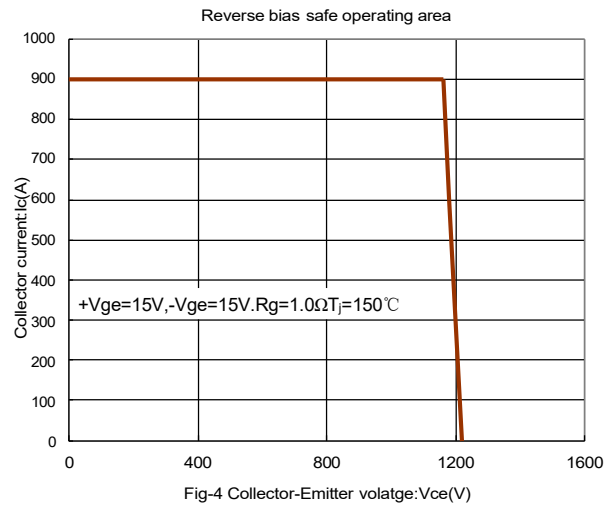
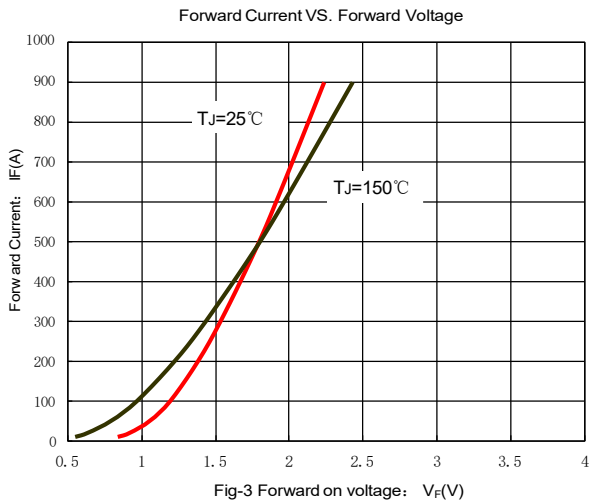
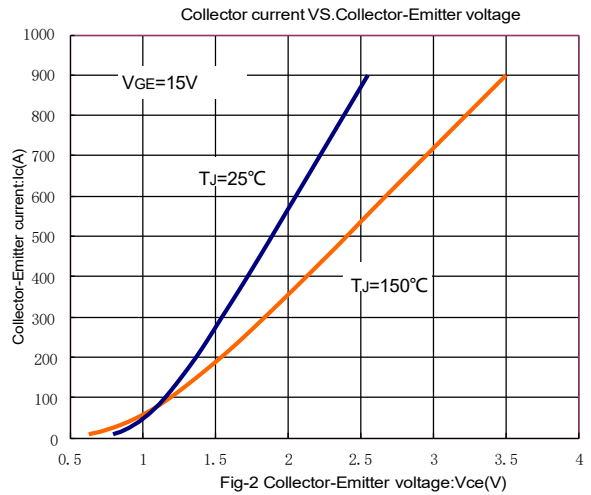
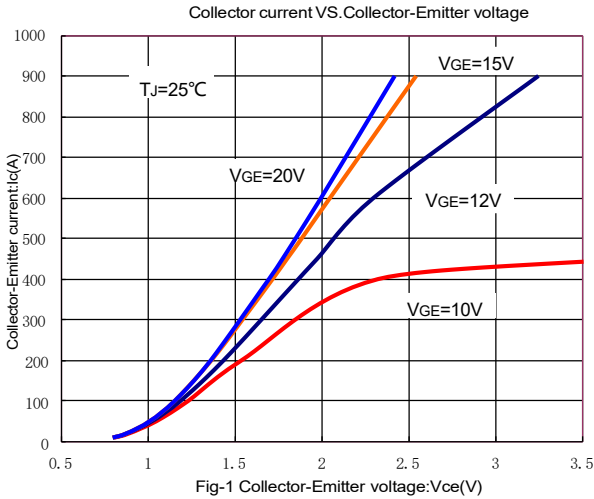
- Low V_{CEsat}
- Standard Housing

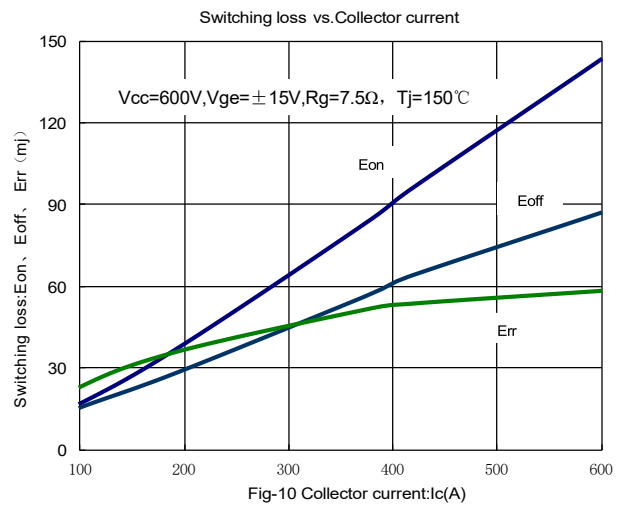
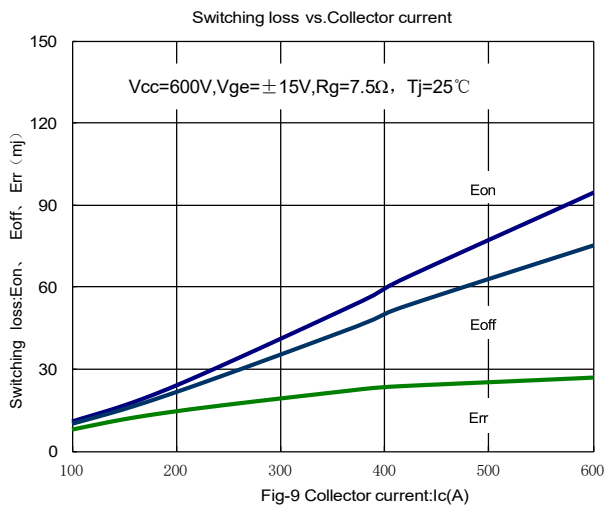
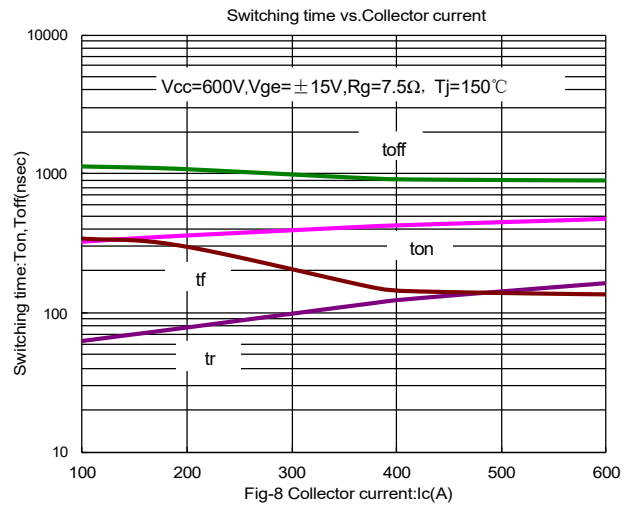
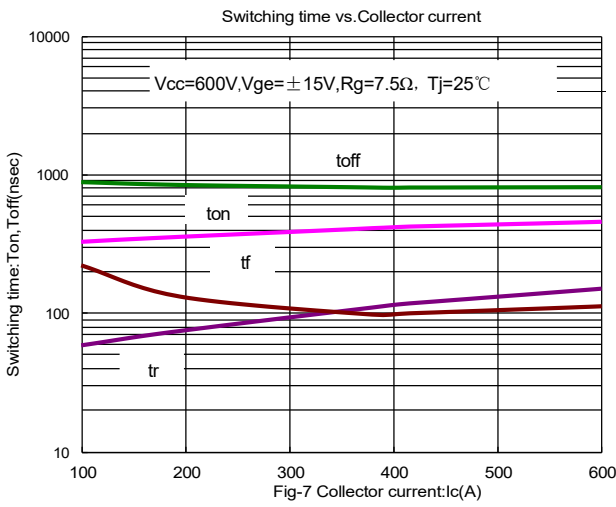
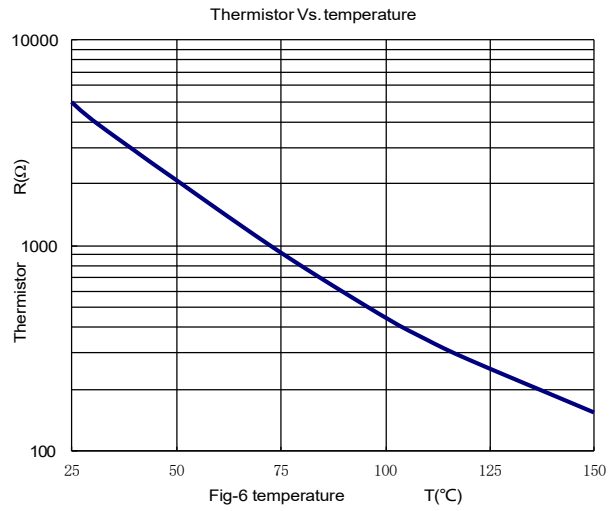
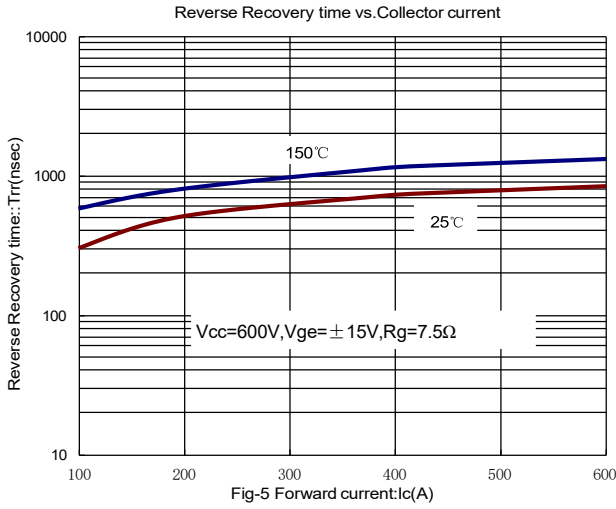
Typical Applications :

- Motor Drive
- Servo Drive
- Uninterruptible Power Supply System
- Wind Turbines
- High Power Converters

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VALUE			UNIT
			Min	Type	Max	
V_{CES}	Collector-Emitter voltage	$T_j=25^{\circ}C$			1200	V
V_{GES}	Gate-Emitter voltage	$T_j=25^{\circ}C$			± 20	V
I_c	Collector current	Continuous@ $T_c=80^{\circ}C$			450	A
I_{CP}		$T_P=1ms$			900	A
P_C	Collector power dissipation	$T_j=25^{\circ}C, 1 \text{ device}$			2100	W
T_{Vjop}	Junction temperature	/	-40		125	$^{\circ}C$
T_{stg}	Storage temperature	/	-40		125	$^{\circ}C$
V_{iso}	Isolation between terminal and copper base	$T_j=25^{\circ}C, AC: 1 \text{ minute}$	2500			V
I_{CES}	Zero gate voltage collector current	$T_j=25^{\circ}C, V_{CE}=1200V, V_{GE}=0V$			5.0	mA
I_{GES}	Gate-Emitter leakage current	$T_j=25^{\circ}C, V_{CE}=0V, V_{GE}=\pm 20V$			0.4	μA
$V_{GE(th)}$	Gate-Emitter threshold voltage	$T_j=25^{\circ}C, V_{CE}=20V, I_c=18mA$	5.0	5.8	6.5	V
$V_{CE(sat)}$	Collector-Emitter saturation voltage	$T_j=25^{\circ}C, V_{GE}=15V, I_c=450A$		1.70	2.15	V
		$T_j=125^{\circ}C, V_{GE}=15V, I_c=450A$		2.00		V
		$T_j=150^{\circ}C, V_{GE}=15V, I_c=450A$		2.05		V
Q_G	Gate charge	$V_{GE}=\pm 15V$		4.30		μC
R_{Gint}	Internal gate resistor	$T_j=25^{\circ}C$		1.7		Ω
C_{ies}	Input capacitance	$T_j=25^{\circ}C, V_{CE}=25V, V_{GE}=0V, f=1MHz$		32.0		nF
C_{res}	Reverse transfer capacitance			1.5		nF
t_{on}	Turn-on time	$V_{CC}=600V, I_c=450A, V_{GE}=\pm 15V, R_g=7.5\Omega,$ Inductive load, $T_j=150^{\circ}C$		430		ns
t_r	Rise time			120		ns
t_{off}	Turn-off time			900		ns
t_f	Fall time			150		ns
E_{on}	Turn-on energy loss per pulse			95		mJ
E_{off}	Turn-off energy loss per pulse			65		mJ
I_{sc}	Short circuit		$T_j=125^{\circ}C, V_{CC}=900V, V_{GE}\leq 15V$		1800	
t_{sc}	Short circuit withstand time	$T_j=150^{\circ}C, V_{CC}=720V, V_{GE}=\pm 15V, R_g=7.5\Omega$	10			μs
V_F	Forward on voltage	$I_F=450A, T_j=25^{\circ}C$		1.65	2.15	V
		$I_F=450A, T_j=125^{\circ}C$		1.65		V
		$I_F=450A, T_j=150^{\circ}C$		1.62		V
I_{RM}	Peak reverse recovery current	$I_F=450A, -diF/dt=7800A/\mu s (T_{vj}=125^{\circ}C),$ $V_R=600V, V_{GE}=-15V, T_j=125^{\circ}C$		405		A
Q_r	Recovered charge			85.0		μC
E_{rec}	Reverse recovery energy	$V_{CC}=600V, I_c=450A, \text{ Inductive load, } T_j=150^{\circ}C$		55		mJ
t_{rr}	Reverse recovery time	$I_F=450A$	$T_j=25^{\circ}C$		750	ns
			$T_j=125^{\circ}C$		1100	ns

R _{th(j-c)}	Thermal resistance(1 device)	IGBT			0.06	°C /W
		FWD			0.10	°C /W
R _{th(c-H)}	Thermal resistance, case to heatsink	per module		0.009		°C /W
R ₂₅	Rated resistance	T _C =25°C		5.0		kΩ
ΔR/R	Deviation of R100	T _C =100°C, R ₁₀₀ =493 W		-5	5	%
P ₂₅	Power dissipation	T _C =25°C			20	mW
B _{25/50}	B-value	R ₂ =R ₂₅ exp [B _{25/50} (1/T ₂ -1)/(298,15 K)]		3375		K
B _{25/80}	B-value	R ₂ =R ₂₅ exp [B _{25/80} (1/T ₂ -1)/(298,15 K)]		3411		K
B _{25/100}	B-value	R ₂ =R ₂₅ exp [B _{25/100} (1/T ₂ -1)/(298,15 K)]		3433		K
Screw torque	Mounting(M5)	/	2.4		3.0	N·m
	Terminals(M6)	/	3.5		5.0	N·m
W _t	Weight				345	g
Outline	M43					





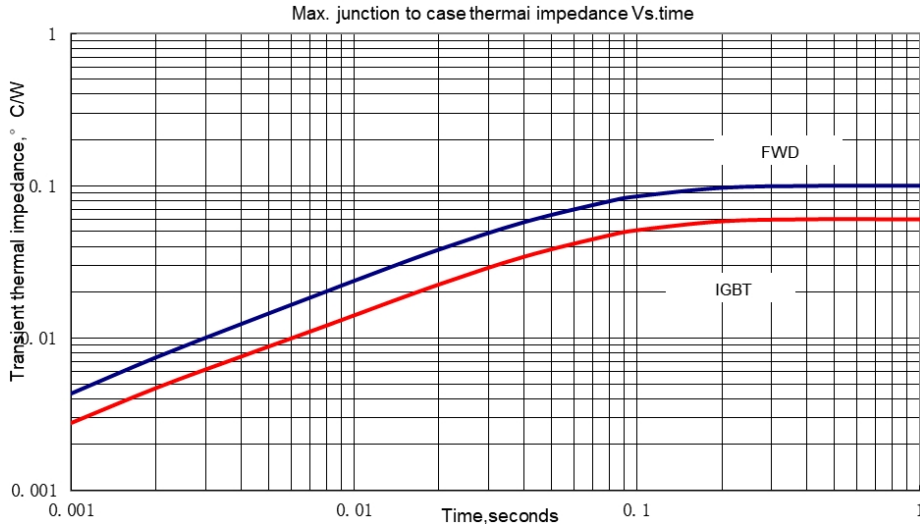
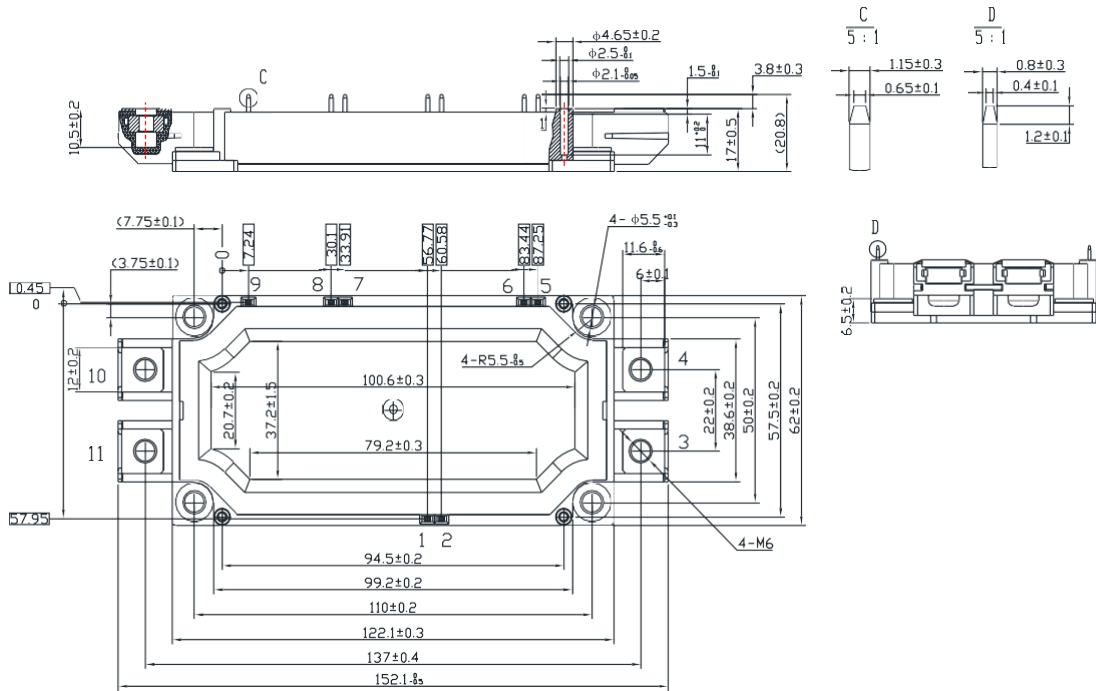
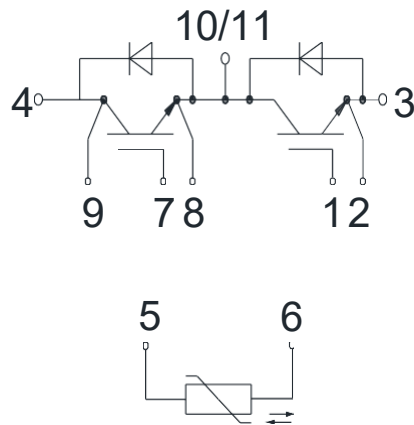


Fig-11

Outline & Circuit Diagram



MD450MB120CS



Unmarked dimensional tolerance: $\pm 0.5\text{mm}$

NIPS reserves the right to change specifications without notice.